

## 6 Element SMD Phototransistor Array

### Features

- High speed phototransistor OL8110 chips
- Reference holes for precise mounting
- Compact size and low cost
- Also available with mounted reticle
- Custom design available
- Single chip placement for high speed applications



### Application

- Optical Encoders (absolut, incremental, multi turn)
- Edge detection for paper
- Multi Element Sensor Array

### Absolute Maximum Ratings

Storage and Operating Temperature	-35 to +85 °C (*)
Solder Temperature (Vapor Phase Reflow for 30 sec)	235 °C

(\*) Military Temperature range available on request

### Electrical Specifications (T<sub>A</sub> = 25°C)

- Parameters 100% tested at waferprobe

Parameter	Units	Min	Typ	Max
I <sub>CEO</sub> @ 52.0 V	µA		0.1	100.0
I <sub>DARK</sub> @ 32.0 V	nA		1.0	100.0
I <sub>ECO</sub> @ 7.7 V	µA		0.1	100.0
V <sub>CESt</sub> (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 22.2 µA)	mV		290.0	400.0
HFE (I <sub>C</sub> = 2.0 mA, V <sub>CE</sub> = 5.0 V)		500.0	750.0	1000.0

### Additional Parameters tested for qualification and on a lot sample basis

- Rise time: 10.0 µs (V<sub>CC</sub> = 5.0 V, R<sub>L</sub> = 1.2 kΩ, C<sub>L</sub> = 8.0 pF, V<sub>E(peak)</sub> = 1.0 V)
- Fall time: 13.0 µs (V<sub>CC</sub> = 5.0 V, R<sub>L</sub> = 1.2 kΩ, C<sub>L</sub> = 8.0 pF, V<sub>E(peak)</sub> = 1.0 V)
- Responsivity peak wavelength: 880 nm

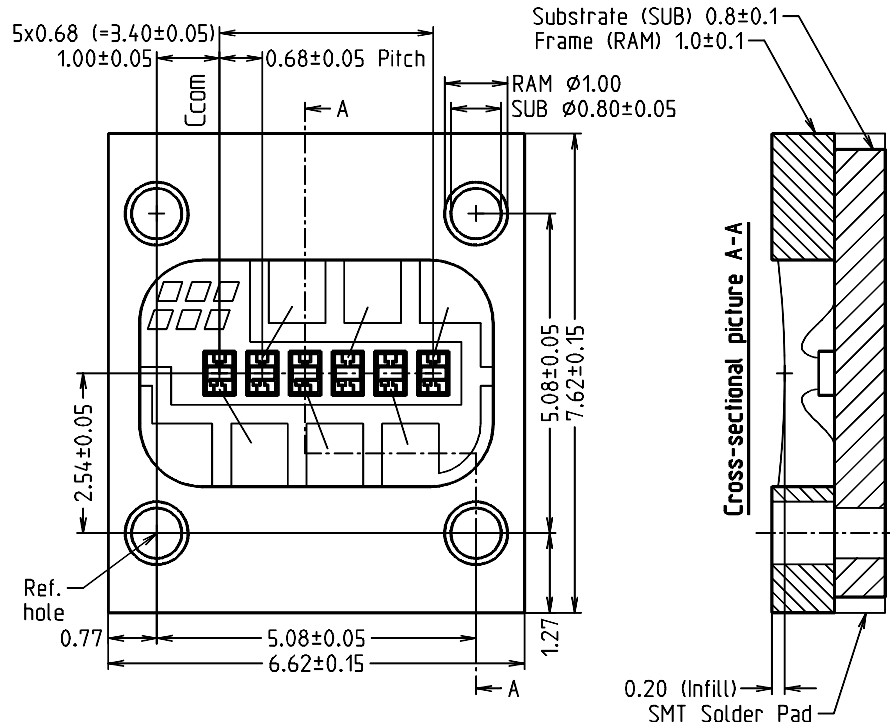
### Note

Please see part **ET8001**, precision schmitt trigger and comparator array with hysteresis tracking function for use with this phototransistor array.

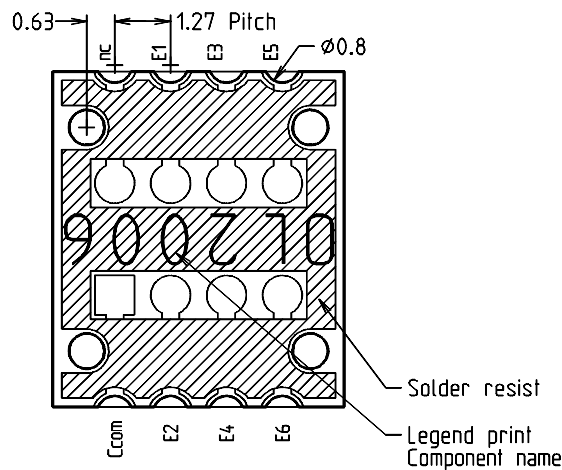
# OL2006

## 6 Element SMD Phototransistor Array

### Top view



### Bottom view



Chip type:  
OL8110 (6x) Phototransistor  
Chip thickness: 178µm - 254µm

